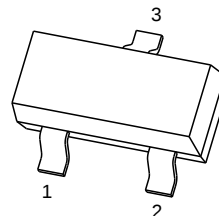


SOT-23 Plastic-Encapsulate MOSFETS

BSS123 N Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100 V	6Ω@10V	0.17A
	10Ω@4.5V	

SOT-23



- 1. GATE
- 2. SOURCE
- 3. DRAIN

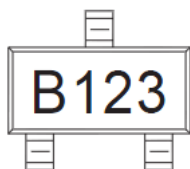
FEATURE

Surface Mount Package
High Density Cell Design for Extremely Low $R_{DS(ON)}$
Voltage Controlled Small Signal Switch
Rugged and Reliable

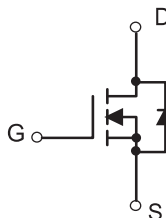
APPLICATION

Small Servo Motor Controls
Power MOSFET Gate Drivers
Switching Application

MARKING



Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
N-MOSFET			
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (note 1)	I_D	0.17	A
Pulsed Drain Current ($t_p=10\mu\text{s}$)	I_{DM}	0.68	A
Continuous Source-Drain Diode Current	I_S	0.17	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

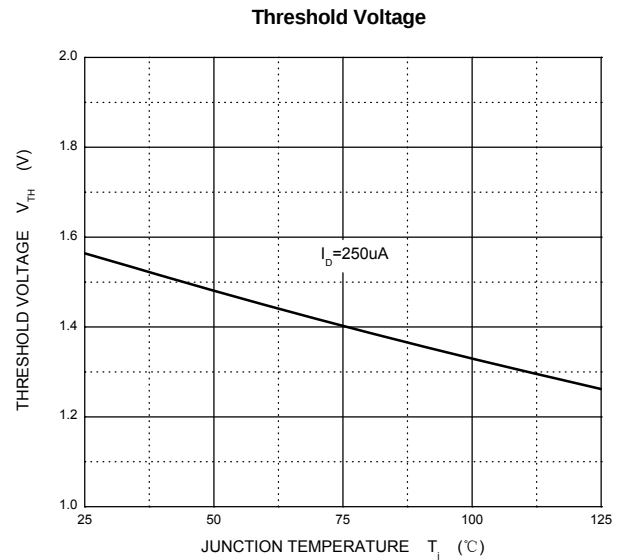
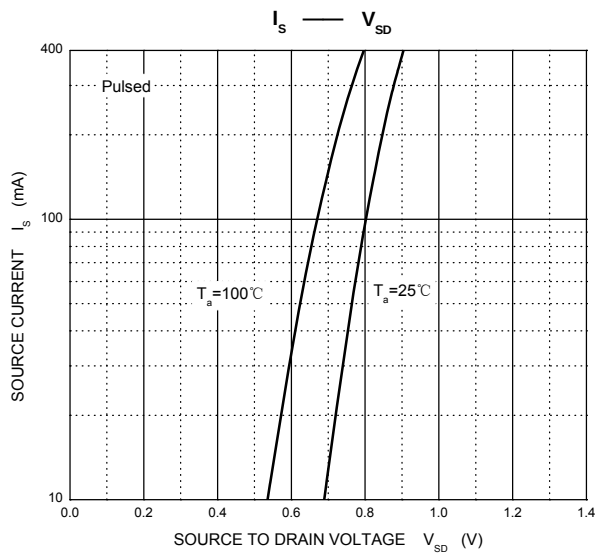
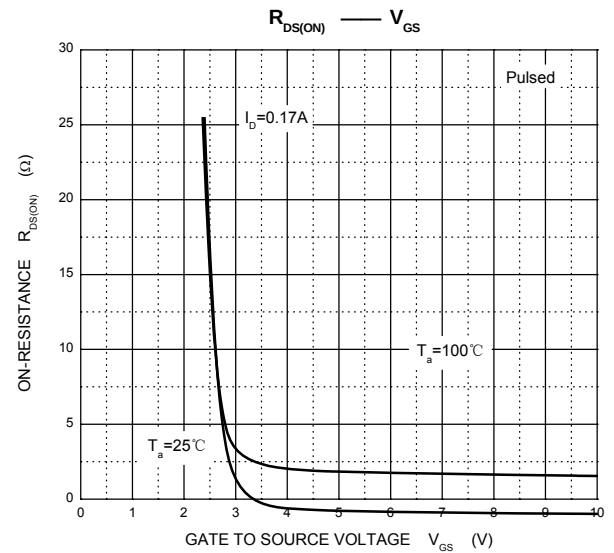
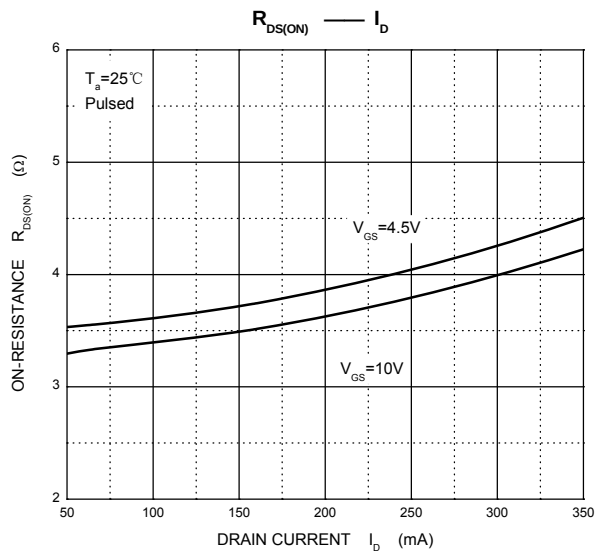
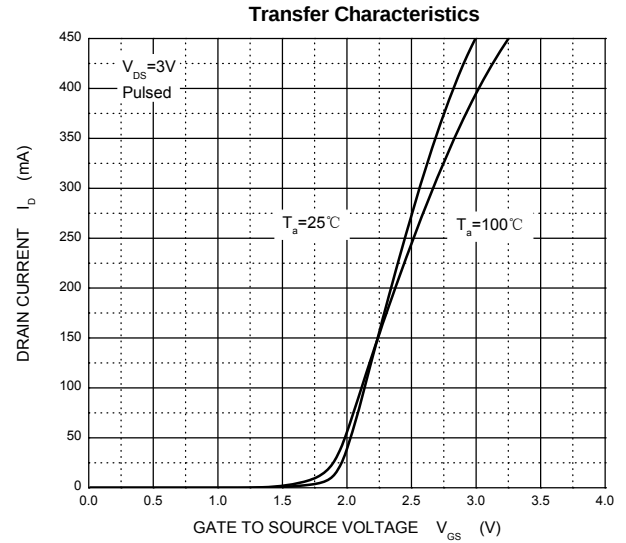
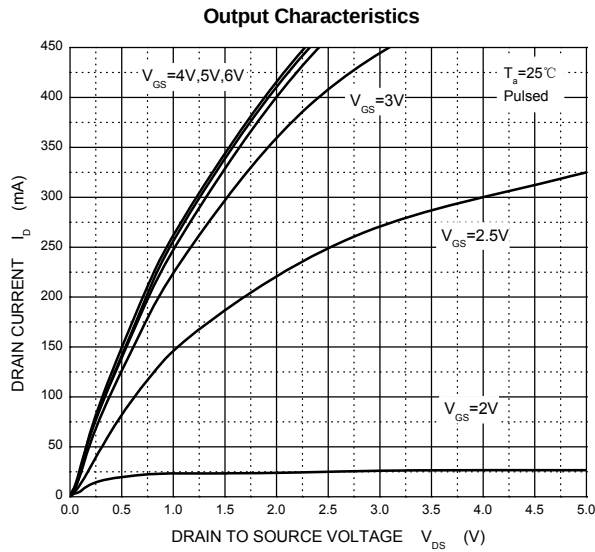
$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	100			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =100V, V _{GS} = 0V			1	μA
		V _{DS} =20V, V _{GS} = 0V			10	nA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			±50	nA
Gate threshold voltage (note 2)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.6	2.8	V
Drain-source on-resistance(note 2)	R _{DS(on)}	V _{GS} =4.5V, I _D =0.17A		3.8	10	Ω
		V _{GS} =10V, I _D =0.17A		3.5	6	Ω
Forward tranconductance(note 2)	g _{FS}	V _{DS} =10V, I _D =170mA	80			mS
Diode forward voltage	V _{SD}	I _S =340mA, V _{GS} = 0V			1.3	V
DYNAMIC CHARACTERISTICS (note 4)						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f =1MHz		29	60	pF
Output Capacitance	C _{oss}			10	15	pF
Reverse Transfer Capacitance	C _{rss}			2	6	pF
SWITCHING CHARACTERISTICS (note 3,4)						
Turn-on delay time	t _{d(on)}	V _{GS} =10V, V _{DD} =30V, I _D =0.28A, R _{GEN} =50 Ω			8	ns
Turn-on rise time	t _r				8	ns
Turn-off delay time	t _{d(off)}				13	ns
Turn-off fall time	t _f				16	ns
Total Gate Charge	Q _g	V _{DS} =10V, I _D =0.22A, V _{GS} =10V		1.4	2	nC
Gate-Source Charge	Q _{gs}			0.15	0.25	nC
Gate-Drain Charge	Q _{gd}			0.2	0.4	nC

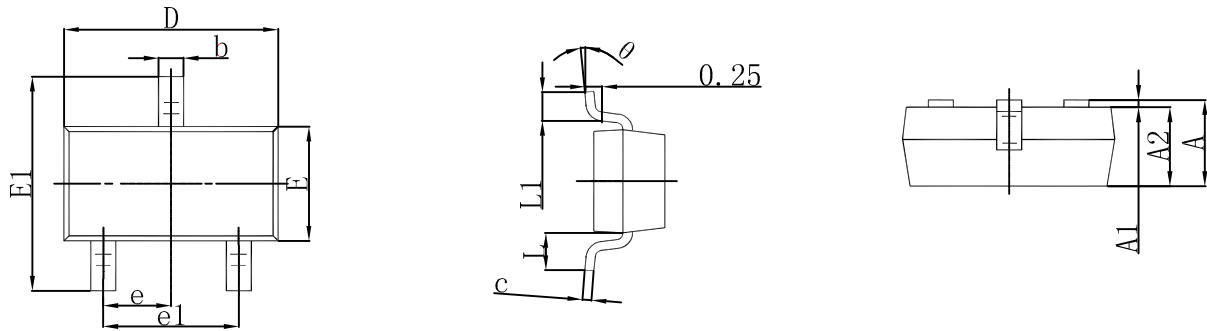
Notes :

1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse width=300 μ s, duty cycle $\leq$ 2%.
3. Switching characteristics are independent of operating junction temperature.
4. Graranted by design, not subject to producing.

Typical Characteristics

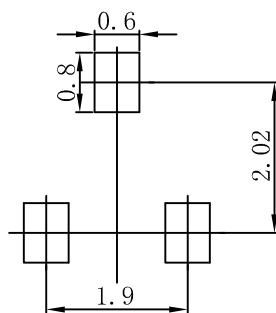


SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.